Q. Code:279899							
	Reg. No.				PART- B (5 x 14 =		
B.E / B.TECH. DEGREE EXAMINATION, MAY 2023 Second Semester PH18252 - PHYSICS OF MATERIALS				11(a)	(i) Obtain Wiedemann Franz Law by de electrical and thermal conductivity an		
	(Common to BIO, ECE &EEE) (Regulation 2018 & 2018A)				Lorentz number.		
TIN	IE: 3 HOURS MAX. I	MARK	S: 100		(ii) The electrical resistivity of copper at 27°Cits thermal conductivity if the Lorentz nu		
CO 2	 Comprehend the behavior of electrons in solids. Demonstrate an understanding of various properties of Semiconducting ma internal structure. 	terials	and their	11(b)	 (O) 1(b) (i) Explain with suitable diagram how do function varies with temperature. (ii) Derive an expression for the Density calculate the carrier concentration in metabolic concentr		
CO : CO :	 Students will get the exposure of the dielectric properties and material and materials in various fields. Summarize basics of magnetism and superconductivity. Explore a few of the applications. Develop an understanding the applications of Nano materials and new engineer. 	its ap fir tech	plications mological aterials in				
	various fields.	g		12(a)	Explain the terms conduction band and val		
	PART- A (10 x 2 = 20 Marks) (Answer all Questions)			(()	semiconductor with a diagram. Deduce an concentration of an electron in intrinsic semico		
		CO	RBT LEVEL		(OR		
1	What are the merits of classical free electron theory?	1	2	12(b)	Obtain an expression for Hall coefficien		
2	Evaluate the average energy of a free electron at 0K while the fermi energy of a free electron at 0K.	1	4	()	semiconductors. Mention the applications of H		
3	Compared with Germanium, silicon is widely used to manufacture the elemental device?	2	3	13(a)	Mention the different mechanisms of polariza		
4	Given an extrinsic semiconductor, how will you find whether it is n-type or p- type?	2	3		(OR)		
5	Distinguish between Lorentz force and Coulomb force in dielectrics.	3	3	13(b)	Derive an expression for the Local field in a die		
6	Calculate the electronic polarizability of neon. The radius of neon atom is 0.158	3	3		Deduce Clausius-Mosotti equation.		
7	IIII.	4	4	14(a)	(i) Distinguish between Type-I and Type-II		
/ 0	What is meant by energy product? What do you infor from it?	4	4		(ii) A train runs without wheel-Interpret its p		
ð	List out the various forms of earbon nonetyles	4	5		(OR)		
9 10	Elucidate why cryotron is referred as a switching device?	5 5	4	14(b)	(i) Give the classification of magnetic material susceptibility.		
					(ii) Distinguish between soft and hard magnet		

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14 = 70 Marks)			
	Marks	CO	RBT LEVEL
by deriving the expressions of ty and find the expression for	(12)	1	3
tt 27°C is $1.72 \times 10^{-8} \Omega$ m. Compute ntz number is 2.26 x $10^{-8} W \Omega K^{-2}$	(2)	1	3
(OK) does Fermi energy distribution	(4)	1	3
sity of states and based on that n metals.	(10)	1	3
d valence band of an intrinsic e an expression for the carrier emiconductor.	(14)	2	4
(OR) ficient for n-type and p-type s of Hall Effect.	(14)	2	4
olarization in different dielectric xpressions.	(14)	3	3
a dielectric for a cubic structure.	(14)	3	3
pe-II superconductors.	(7)	4	2
t its principle and working.	(7)	4	2
(OR) materials on the basis of magnetic	(7)	4	2
nagnetic materials.	(7)	4	2

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15(a)	(i)	Discuss in detail the production and properties of Bucky balls.	(7)	5	3		
	(ii)	Explain any one method for preparation of carbon nanotubes and give	(7)	5	3		
		their important properties					
(OR)							
15(b)	(i)	What are intelligent materials why they are called so?	(4)	5	2		
	(ii)	Describe the characteristics of intelligent materials. List out any four	(10)	5	2		
		Applications.					

<u>PART- C (1 x 10 = 10 Marks)</u>

(Q.No.16 is compulsory)

			Marks	CO	RBT
					LEVEL
16	(i)	Explain how band gap of a semiconducting material can be	(6)	2	3
		determined experimentally?			
	(ii)	Sketch hysteresis curve and mark 'retentivity' and 'coercivity'.	(4)	4	3

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